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**Theory and applications of the Ion Beam  
Induced Charge (IBIC) technique**

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*"I may not have gone where I intended to go,  
but I think I have ended up where I needed to be".*

*Douglas Adams  
The long dark tea-time of the soul  
1988*



# Table of Contents

<b>Table of Notations</b>	13
<b>Preface</b>	15
<b>Chapter 1</b> <i>The Ion Beam Induced Charge microscopy</i>	17
<b>1.1 The interaction of MeV ions with matter</b>	18
1.1.1 Nuclear and electronic energy loss	18
1.1.2 Electron-hole pair creation	19
<b>1.2 The IBIC technique</b>	20
1.2.1 The IBIC set-up	20
1.2.2 The interpretation of the IBIC signal	23
<b>1.3 Applications of IBIC microscopy</b>	24
1.3.1 Characterization of the electronic properties of semiconductors	24
1.3.2 Technological applications and future challenges	28
<b>1.4 Discussion</b>	29
<b>Chapter 2</b> <i>Charge induction in semiconductor detectors</i>	31
<b>2.1 Charge induction in semiconductor detectors</b>	31
2.1.1 Energy balance of the system	31
2.1.2 The instantaneously induced charge	37
2.1.3 Contribution of the Gunn's term to the induced charge pulse formation	39
2.1.4 An equation for the weighting potential	44
2.1.5 Weighting field and capacitance	46
2.1.6 Contribution of the coupling term to the induced charge pulse formation	48

<b>2.2 Examples and applications</b>	<b>55</b>
2.2.1 Parallel plate capacitor	55
2.2.2 Abrupt Schottky junction in an ideal diode	57
<b>2.3 Induced charge sharing in Gunn's theory</b>	<b>57</b>
2.3.1 Definitions and general properties	58
2.3.2 Charge sharing in a <i>N</i> -electrode device	60
2.3.3 Charge sharing for position sensitive radiation detection	67
2.3.4 Topological approach to charge sharing position sensitive detectors	68
 <b>Chapter 3</b>	 <b>71</b>
<i>Numerical tools for the simulation of IBIC experiments</i>	
<b>3.1 Simulation tools and simulation strategies</b>	<b>71</b>
<b>3.2 The adjoint equation method</b>	<b>75</b>
3.2.1 The adjoint equation strategy	75
3.2.2 The adjoint continuity equation	77
3.2.3 CCE profile of an ideal one-dimensional n-type Schottky junction	83
<b>3.3 The Monte Carlo method</b>	<b>88</b>
3.3.1 The Monte Carlo approach	89
3.3.2 One-dimensional stochastic charge transport simulation	90
3.3.3 Monte Carlo approach in higher dimensional geometries	94
3.3.4 Discussion	98
 <b>Chapter 4</b>	 <b>99</b>
<i>Modeling of IBIC experiments for the characterization of semiconductor devices</i>	
<b>4.1 Lateral IBIC characterization of a 4H-SiC Schottky diode</b>	<b>99</b>
4.1.1 Experimental	100
4.1.2 Modeling	106
4.1.3 Discussion	111

<b>4.2 Lateral IBIC characterization of a p-type diamond Schottky diode</b>	112
4.2.1 Experimental	112
4.2.2 Modeling	115
4.2.3 Discussion	119
<b>4.3 Monte Carlo analysis of a charge sharing based p-i-n Si position sensitive particle detector</b>	120
4.3.1 Experimental	122
4.3.2 Modeling	123
4.3.3 Position sensitive ion detection	129
4.3.4 On the improvement of the position sensitivity resolution	131
4.3.5 Discussion	133
<b>Chapter 5</b>	135
<i>Ion beam microfabrication and IBIC characterization of diamond particle detectors</i>	
<b>5.1 IBIC characterization of a diamond particle detector with buried graphitic micro-electrodes</b>	136
5.1.1 Experimental	137
5.1.2 Modeling	143
5.1.3 Discussion	144
<b>5.2 Charge transport properties in the cap-layer of an ion-beam micro-fabricated diamond detector</b>	145
5.2.1 Experimental	146
5.2.2 Modeling	150
5.2.3 Discussion	152
<b>5.3 Characterization of an ion-beam-micromachined multi-electrode diamond detector</b>	153
5.3.1 Samples and electrical characterization	155
5.3.2 IBIC characterization	156
5.3.3 Discussion	161
<b>5.4 Sharing of anomalous polarity pulses in an ion-beam-micromachined multi-electrode diamond detector</b>	162

5.4.1 Theoretical	162
5.4.2 IBIC characterization	165
5.4.3 Discussion	169
<b>Conclusions</b>	<b>171</b>
<b>1. Discussion of results</b>	<b>171</b>
<b>2. Outlook and perspectives</b>	<b>174</b>
<b>Appendix 1</b>	<b>177</b>
<i>Development of an educational software describing the main features of the IBIC technique</i>	
<b>A1.1 Charged particle in a condenser</b>	<b>178</b>
<b>A1.2 Particles decay in a fully depleted diode</b>	<b>179</b>
<b>A1.3 Charged particles in a partially depleted diode</b>	<b>181</b>
<b>A1.4 Lateral IBIC experiment in a partially depleted diode</b>	<b>182</b>
<b>A1.5 Damaged layer in a fully depleted diode</b>	<b>182</b>
<b>A1.6 Frontal IBIC map of a polycrystalline sample</b>	<b>183</b>
<b>Appendix 2</b>	<b>185</b>
<i>Development of a Monte Carlo parallel code with increased computing performance</i>	
<b>A2.1 The sequential Monte Carlo code</b>	<b>185</b>
<b>A2.2 Parallel execution of the Monte Carlo algorithm</b>	<b>187</b>
<b>A2.3 Performance of the parallel program execution</b>	<b>190</b>
<b>A2.3.1 Number of simulated ions per generation point</b>	<b>191</b>
<b>A2.3.2 Number of generation points</b>	<b>191</b>
<b>A2.3.3 Work-Pool approach and load-balance</b>	<b>193</b>
<b>A2.3.4 Simulation speed-up</b>	<b>195</b>
<b>A2.4 Discussion</b>	<b>197</b>



<b>Appendix 3</b>	199
<i>IAEA Coordinated Research Project: Modeling and validation of ion beam induced damage in semiconductors</i>	
<b>Appendix 4</b>	201
<i>A Monte Carlo software for the simulation of IBIC experiments</i>	
<b>Appendix 5</b>	207
<i>Scientific activities</i>	
<b>Appendix 6</b>	213
<i>Published papers</i>	
<b>Acknowledgements</b>	255
<b>Table of References</b>	259



# Table of Notations

$\Delta x$	Space step on a discrete grid
$\Delta t$	Time step on a discrete grid
$\delta n$ ( $\delta p$ )	Re-distribution of electron (hole) volume density due to charge screening within the Debye's length
$\varepsilon$	Dielectric constant
$\mu_n$ ( $\mu_p$ )	Electron (hole) mobility
$\rho_0$	Volume charge density at the electrostatic equilibrium
$\rho'$	Probe charge density generated within the device volume
$\Sigma_i$	Surface of the $i$ -th Dirichlet integration boundary
$\tau_n$ ( $\tau_p$ )	Electron (hole) lifetime
$\phi_{bi}$	Built-in potential
$\psi_0$	Electric potential at the electrostatic equilibrium
$\psi$	Total electric potential in presence of a volume probe charge density
$\psi'$	Electric potential associated with the volume probe charge density $\psi - \psi_0$
$\Omega$	Device integration volume
$A$	Electrode's surface
$C(V)$	Voltage dependent capacitance
CCE	Charge collection efficiency
$D_n$ ( $D_p$ )	Electron (hole) diffusivity
$d\mathbf{s}$	Integration area element on the electrodes surface
$e$	Absolute value of the elementary electric charge
$\mathbf{E}_0$	Electric field at the electrostatic equilibrium
$\mathbf{E}$	Total electric field in presence of a volume probe charge density
$\mathbf{E}'$	Electric potential associated with the volume probe charge density
$\mathbf{J}_0$	Electric current density at the electrostatic equilibrium
$\mathbf{J}'$	Electric current density of excess charge carriers
$i_j$	Current induced at the $j$ -th electrode
$i_{j,G}$	Contribution of the Gunn's term to the current induced at the $j$ -th electrode
$i_{j,C}$	Contribution of the coupling term to the current induced at the $j$ -th electrode
$L_n$ ( $L_p$ )	Electron (hole) diffusion length
$\mathbf{n}$	Normal vector to the integration domain's bounding surface
$N_D$ ( $N_A$ )	Ionized donor (acceptor) volume density
$n_0$ ( $p_0$ )	Native volume density of free electrons (holes) at the electrostatic equilibrium
$n_{init}$ ( $p_{init}$ )	Native volume density of free electrons (holes) at the electrostatic equilibrium in an unbiased semiconductor
$n'$ ( $p'$ )	Excess electron (hole) volume density generated within the device volume
$n$ ( $p$ )	Total (native and generated) electron (hole) volume density
$n^+$ ( $p^+$ )	Solution of the adjoint electron (hole) continuity equation
$P_{0,n}$ ( $P_{0,p}$ )	Probability for the electron (hole) to remain at the same position during the time interval $\Delta t$

$P_{\pm x,n} (P_{\pm x,p})$	Probability for the electron (hole) to move a step right/left during the time interval $\Delta t$
$P_{dec,p}(\mathbf{x})$	Probability for the electron (hole) to recombine during the time interval $\Delta t$
$\mathbf{Q}$	Total induced charge vector associated with a multi-electrode device
$\mathbf{Q}_{e,h}$	Total induced charge vector associated with electron (hole) motion a multi-electrode device
$Q$	Total charge stored within the device volume
$Q_{j,0}$	Charge bore by the $j$ -th electrode at the electrostatic equilibrium
$Q_j$	Charge instantaneously bore by the $j$ -th electrode
$Q_{j,G}$	Contribution of the Gunn's term to the charge instantaneously bore by the $j$ -th electrode
$Q_{j,C}$	Contribution of the coupling term to the charge instantaneously bore by the $j$ -th electrode
$q$	Point-like probe charge density generated within the device volume
$q_j$	Total charge induced at the $j$ -th electrode by the probe charge distribution
$q_{j,G}$	Contribution of the Gunn's term to the total charge induced at the $j$ -th electrode by the probe charge distribution
$q_{j,C}$	Contribution of the coupling term to the total charge induced at the $j$ -th electrode by the probe charge distribution
$R_{np}$	Linearized Shockley-Read-Hall recombination term
$s_0$	Surface charge density at the Neumann boundaries of a device in electrostatic equilibrium
$t$	Generic time parameter
$t_0$	Instant of excess probe charge density generation
$T$	Integration time associated with the external electronic chain
$V_i$	Voltage applied at the $i$ -th electrode
$\mathbf{v}$	Carriers drift velocity vector
$w$	Depletion region width
$\mathbf{x}$	Generic space coordinates vector
$\mathbf{x}_B$	Space coordinates vector at the volume boundary surface
$\mathbf{x}_I$	Space coordinates vector associated with the initial position of a point-like probe charge
$\mathbf{x}_F$	Space coordinates vector associated with the final position of a point-like probe charge
$\partial\psi_0/\partial V_j$	Weighting potential associated with the $j$ -th electrode
$\partial\mathbf{E}_0/\partial V_j$	Weighting field associated with the $j$ -th electrode

# Preface

The Ion Beam Induced Charge (IBIC) microscopy is an analytical technique that exploits the interaction of MeV ion beams, focused down to a micrometer spot size, with matter to investigate the electronic properties of semiconductor materials and devices.

The reasons for the increasing utilization of the technique for material characterization are given by the wide availability of linear accelerator machines and by the expertise in ionizing radiation detection and signal amplification, both due to the development of nuclear physics research in the past century. On the other hand, the reliability of the IBIC microscopy lies on the existence of a solid theoretical model, allowing to extract from the experimental results almost all the parameters required for the characterization of the electrical and electronic properties of the sample under test.

In my Dissertation, the main features of the IBIC technique are investigated and discussed, together with an overview of the underlying theoretical model and the associated numerical methods for the simulation of experiments.

Theoretical and numerical predictions are tested and validated against experimental data, and are exploited both to perform a characterization of the electronic properties of materials, and to face new challenging applications in physics and technology, such as the development of innovative 2- and 3-dimensional position sensitive ionizing radiation detectors.

In **Chapter 1**, the IBIC microscopy will be introduced in its main features, through the discussion of the underlying physical phenomena, such as ion-matter interaction and charge induction mechanisms, and of the relevant applications in physics experiments and technology development.

In **Chapter 2**, a systematic analysis of the induced charge pulse formation at the electrodes of a semiconductor device is presented. The discussion will focus on charge induction theorems, on relevant application examples and on charge sharing phenomena in multi-electrode devices.

The implementation of the theoretical results for the development of suitable numerical tools to simulate the IBIC signal formation is discussed in **Chapter 3**.

The resulting model, equipped with valuable simulation techniques, will be then validated and exploited in **Chapter 4** in order to model the results of IBIC experiments, aiming at the characterization of emerging wide band-gap semiconductor materials as well as at the optimization of advanced charge sharing particle detection systems.

Finally, **Chapter 5** is devoted to the analysis and the development of novel fully ion-beam-micromachined 3-dimensional diamond particle detectors with integrated graphitic electrodes.